

**Listing of Claims:**

1 – 28. (cancelled)

29. (previously presented) A semiconductor device, comprising:

an NMOS transistor gate structure, the NMOS gate structure comprising a gate dielectric above a semiconductor body, an n-doped first metal silicide structure having a first metal component on, and in direct physical contact with, the gate dielectric; and a second metal silicide having a metal component different from the first metal component, above the n-doped first metal silicide; and

a PMOS transistor gate structure, the PMOS gate structure comprising a gate dielectric above a semiconductor body, a p-doped first metal silicide structure having the first metal component on, and in direct physical contact with, the gate dielectric; and a second metal silicide having a metal component different from the first metal component, above the p-doped first metal silicide.

30. (original) The device of claim 29, wherein the first metal silicide comprises a refractory metal.

31. (original) The device of claim 30, wherein the refractory metal is one of molybdenum, tungsten, tantalum, and titanium.

32. (original) The device of claim 29, wherein the second metal silicide comprises nickel.

33. (previously presented) The device of claim 29, further comprising a silicon layer between the first and second metal silicides in the NMOS and PMOS gate structures.

34-41. (canceled)